

TO-252/TO-251 Plastic-Encapsulate schottky barrier diodes

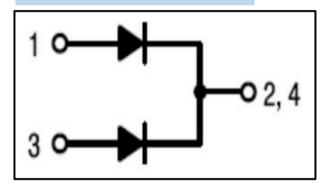
MBR20100CT Dual schottky barrier diodes

QUICK REFERENCE DATA				
VR = 100 V				
IF(AV) = 20 A				
VF ≤ 0.8V				

MECHANICALDATA:

- Case: TO-252/251 molded plastic
- Polarity: As marked.
- Mounting Position: Any
- Weight: 0.0655 ounces, 1.859 grams
- Terminals: solder plated,
 solderable per MIL-STD-750, Method 2026

SYMBOL:

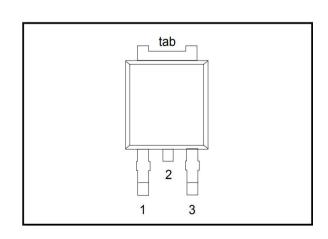


FEATURES:

- Plastic package has Underwriters Laboratory
 Flammability Classification 94V-O
 Flame Retardant Epoxy Molding Compound
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- High current capability
- Guardring for overvlotage protection
- In compliance with EU RoHS 2002/95/EC directives
- For use in low voltage, high frequency inverters free wheeling, and polarlity protection applications.

PINNING:

PIN	DESCRIPTION				
1	anode 1				
2	cathode 1				
3	anode 2				
tab	cathode				





MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%

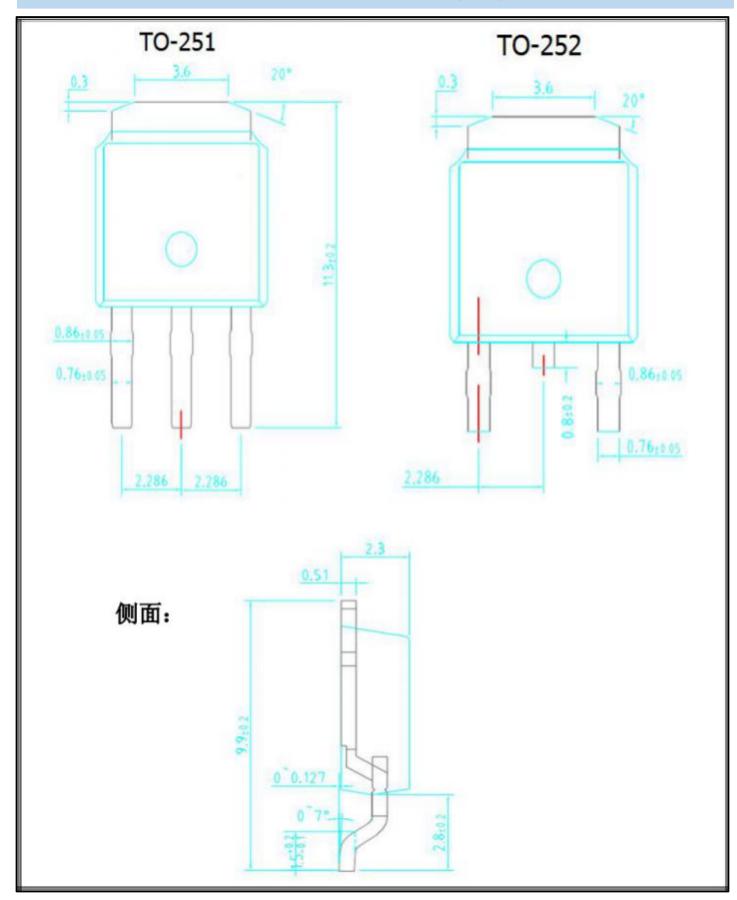
Parameter	Symbol	Test Condition	MIN	TYP	Max	Unit
Peak Repetitive Reverse Voltage	VRRM				100	V
Maxi mum RMS Voltage	VRMS				70	V
Maximum DC Blocking Voltage	VR(DC)				100	V
Average Rectified Forward Current	IF(AV)				20	Α
Peak Forward Surge Current:8.3ms single half sine-	IFSM				200	۸
wave superimposed on rated load (JEDEC method)					200	Α
Maximum Forward Voltage at 10A,per leg	VF				0.8	V
Maximum DC Reverse Current T=25℃	IR			0.05	0.1	mA
at Rated DC Blocking Voltage T=125℃					20	mA
Voltage Rate of Change (Rated VR)	dv/dt				10,000	v/µs
Typical Thermal Resistance	RøJC				2	°C/W
Operating junction temperature	Tj		-65		175	$^{\circ}$
Storage temperature	Tstg		-65		175	$^{\circ}$

Notes:

- 1.Both Bonding and Chip structure are available.
- 2.Pulse Test: Pulse Width = 300 ms, Duty Cycle ≤2.0%
- 3. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: dPD/dTJ < 1/RqJA.



TYPICAL ELEC TRICAL AND THERMAL CHARACTERISTICS





RATING AND CHARACTERISTIC CURVES

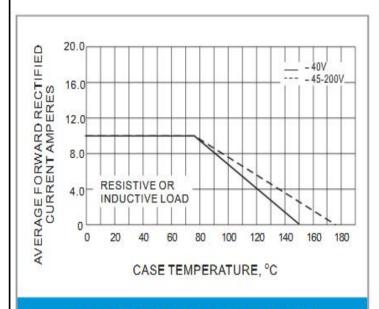


Fig.1- FORWARD CURRENT DERATING CURVE

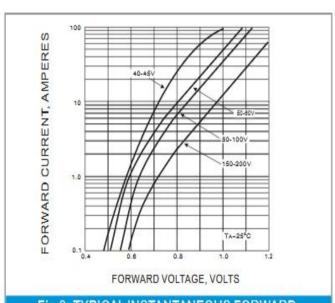


Fig.2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTIC

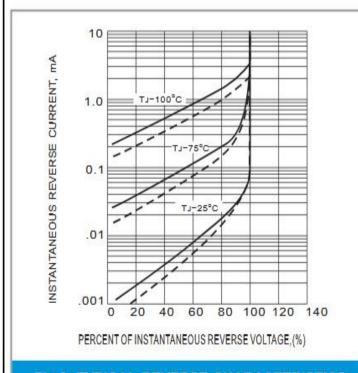
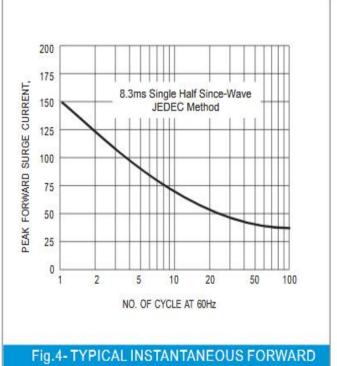


Fig.3- TYPICAL REVERSE CHARACTERISTICS



CHARACTERISTICS